

ABSTRACT OF THE DISCLOSURE

A plurality of boost units are series-connected. A first MOS transistor is connected between one terminal of the series circuit and a VPP node, and the other terminal of the series circuit is connected to the gate of a second MOS transistor for transferring a boosted voltage. Each boost unit is made up of a third MOS transistor having a gate and drain connected to an input portion and a source connected to an output portion, and a capacitor connected to the input portion. The gate of the first MOS transistor is connected to the input portion of an even-numbered boost unit from the VPP node. This realizes high boosting ability, high voltage transfer capacity, and a low power supply voltage.

10083552-022702